



### Description

The IRFZ44EPBF uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.



**TO-220**

### General Features

$V_{DS} = 60V, I_D = 60A$

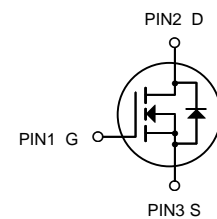
$R_{DS(ON)} < 18m\Omega @ V_{GS}=10V$

### Application

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast



N-Channel MOSFET

**Units Tube**

### Package Marking and Ordering Information

Product ID	Pack	Brand	Units Tube
IRFZ44EPBF	TO-220C	HXY MOSFET	50

### Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	+20	V
$I_D@T_C=25^\circ C$	Drain Current	60	A
IDM	Pulsed Drain Current <sup>1</sup>	240	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	120	W
TSTG	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C



**Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage <sup>(Note 1)</sup>	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	60	68	-	nA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	-	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =25A	-	12	18	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =40A	15	-	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1.0MHz	-	4050	-	PF
Output Capacitance	C <sub>oss</sub>		-	430	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	110	-	PF
<b>Switching Characteristics</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =40A R <sub>G</sub> =50Ω <sup>(Note 2)</sup>	-	60	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	185	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	75	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	60	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =40A, V <sub>GS</sub> =10V <sup>(Note 2)</sup>	-	39	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	9.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	13	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =60A	-	-	1.5	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	60	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.



Typical Electrical

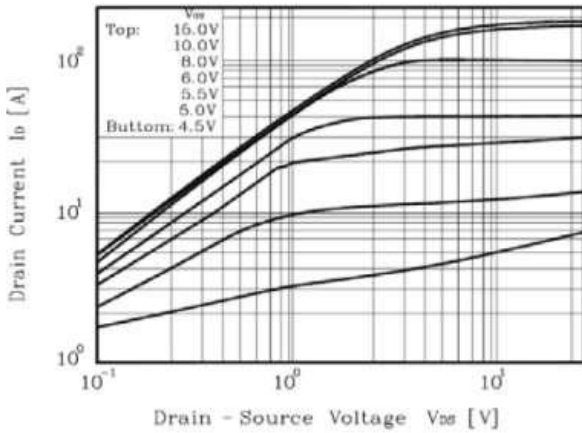


Figure 1. On Region Characteristics

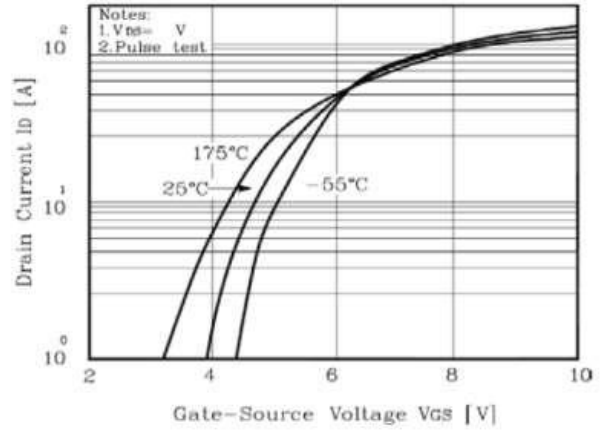


Figure 2. Transfer Characteristics

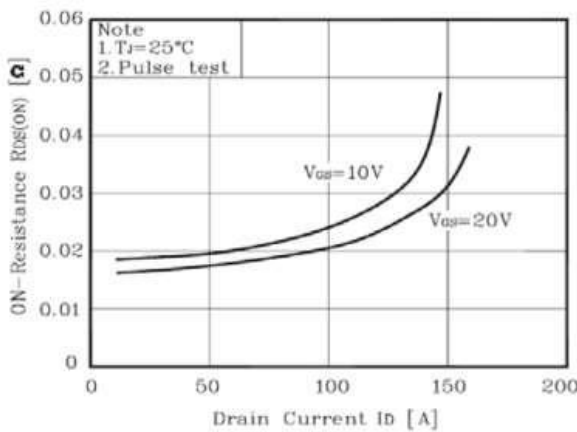


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

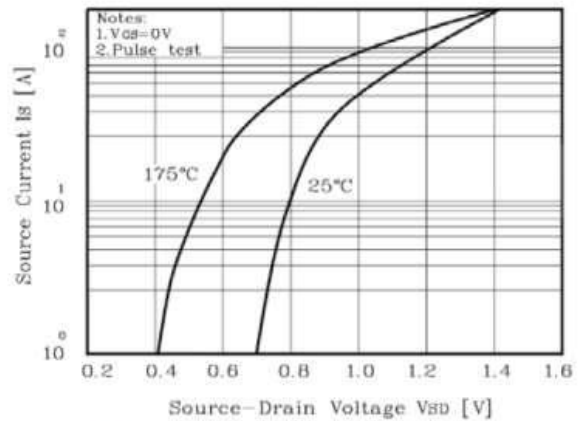


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

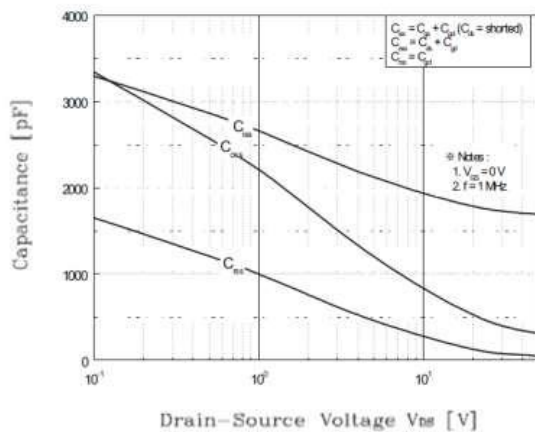


Figure 5. Capacitance Characteristics

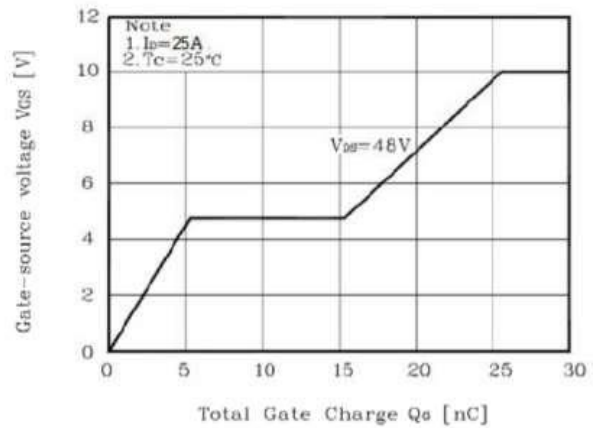


Figure 6. Gate Charge Characteristics

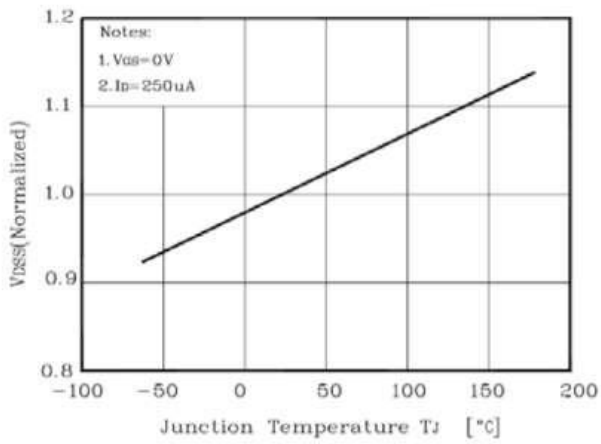


Figure 7. Breakdown Voltage Variation vs Temperature

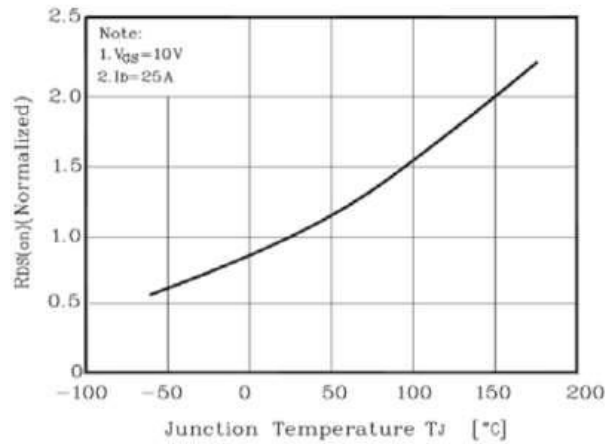


Figure 8. On-Resistance Variation vs Temperature

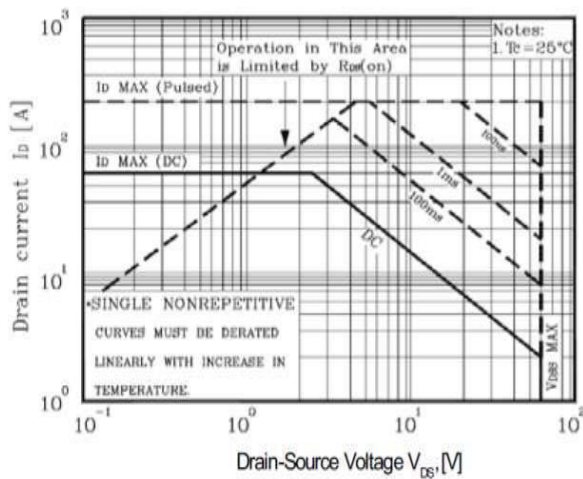


Figure 9. Maximum Safe Operating Area

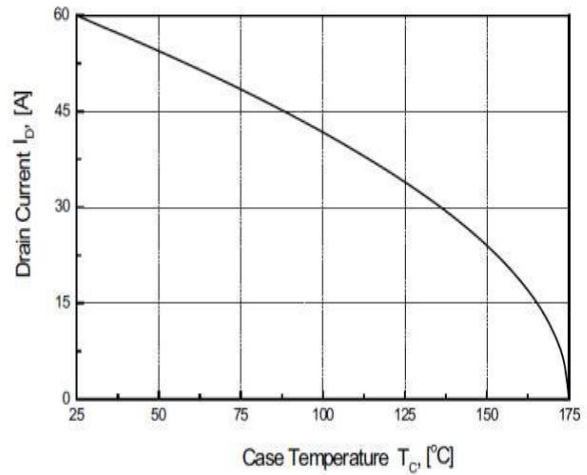


Figure 10. Maximum Drain Current vs Case Temperature

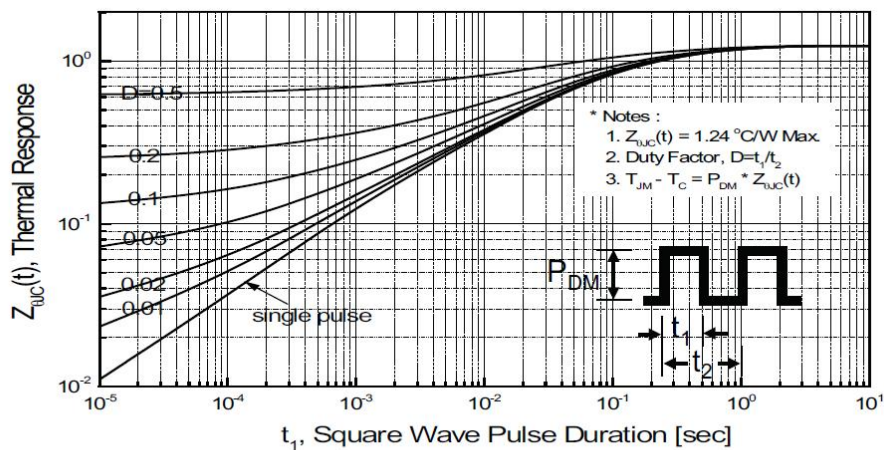
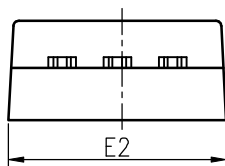
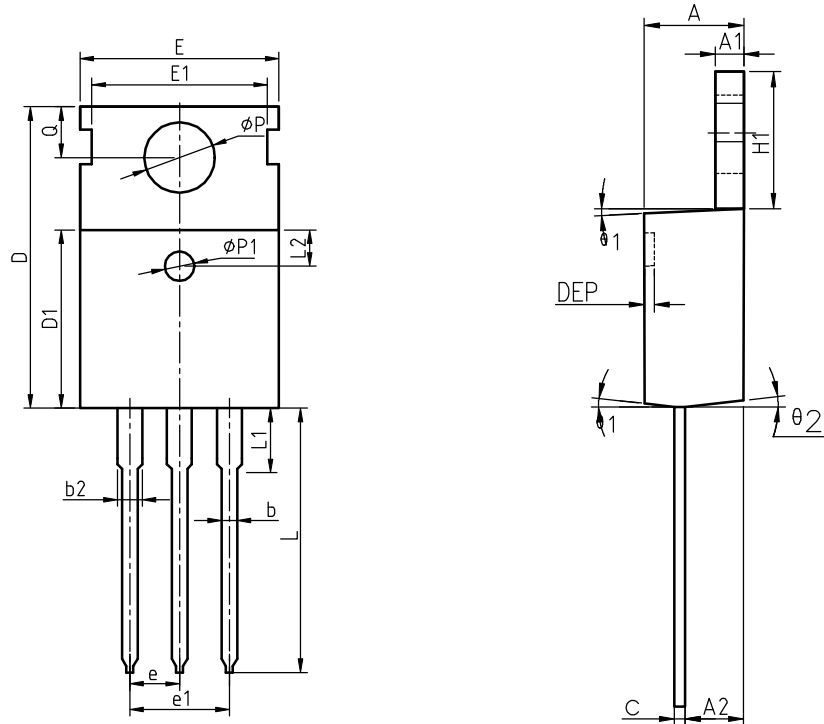


Figure 11. Transient Thermal Response Curve



Package Information  
TO-220C



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
theta 1	5°	7°	9°	5°	7°	9°
theta 2	1°	3°	5°	1°	3°	5°
theta 3	1°	3°	5°	1°	3°	5°



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